

10 / 722 647
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	10 / 722 647
				Filing Date	
				First Named Inventor	Chih-Yuan HSIAO
				Art Unit	2822
Examiner Name					
Sheet	1	of	1	Attorney Docket Number	10113231

U.S. PATENT DOCUMENTS					
Examiner Initials	Cite No.	Document Number (Number – kind code)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Passages or Relevant Figures Appear
MT	A1	US 6,432,774 B2	08/13/2002	Heo et al	
MT	A2	5,519,236	05/21/1996	Ozaki	
	A3				
	A4				
	A5				
	A6				
	A7				

FOREIGN PATENT DOCUMENTS						
Examiner Initials	Cite No.	Document Number (Number – kind code)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Passages or Relevant Figures Appear	T
	B1					
	B2					
	B3					
	B4					

OTHER PRIOR ART			
Examiner Initials	Cite No.	Include name of author (in CAPS), title of article (when appropriate), title of the item (book, magazine, symposium, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T
MT	C1	DEBRA S. WOOLSEY, 'Enhanced discrete DMOS power trench gate oxide growth', <i>Solid State Technology</i> , Volume 45, Issue 8, August 2002, Pennwell Publishing, US	
	C2		
	C3		
	C4		
	C5		

Form PTO/SB/08A & B (modified)

(v08/25/2002)

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